

**SANYO**

No.4647

**2SK1896**

N-Channel MOS Silicon FET

DC-DC Converter,  
Motor Drive Applications**Features**

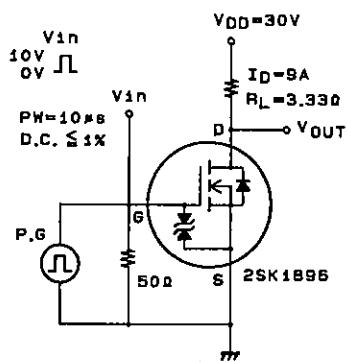
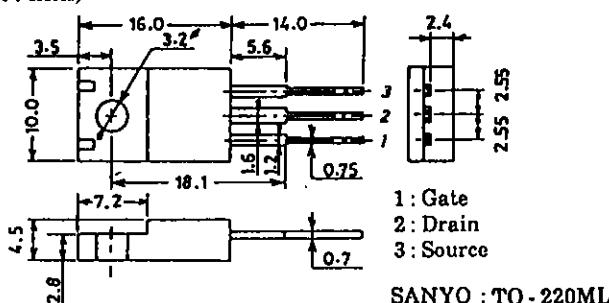
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	60	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current(DC)	I <sub>D</sub>	15	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	A
Allowable Power Dissipation	P <sub>D</sub>	60	W
		2.0	W
		25	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

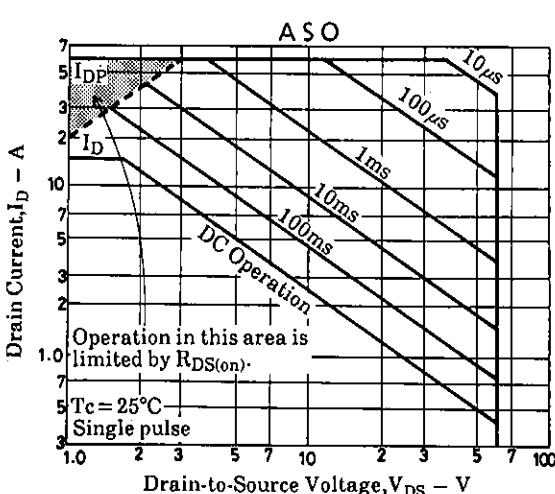
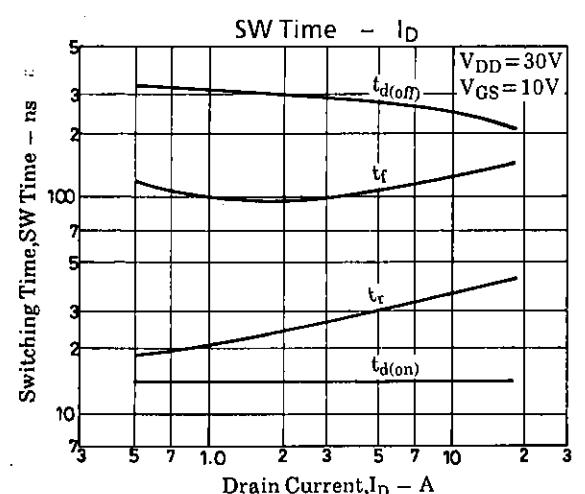
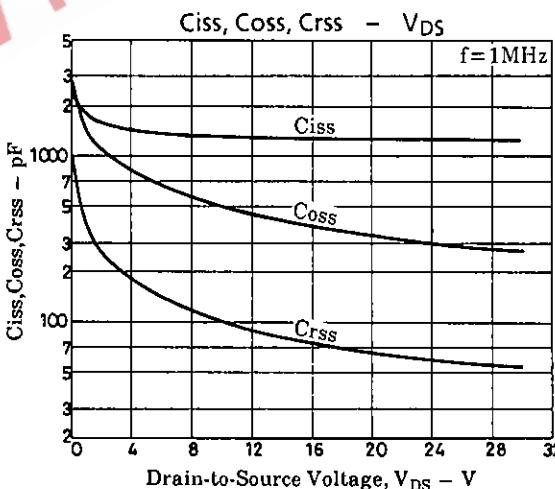
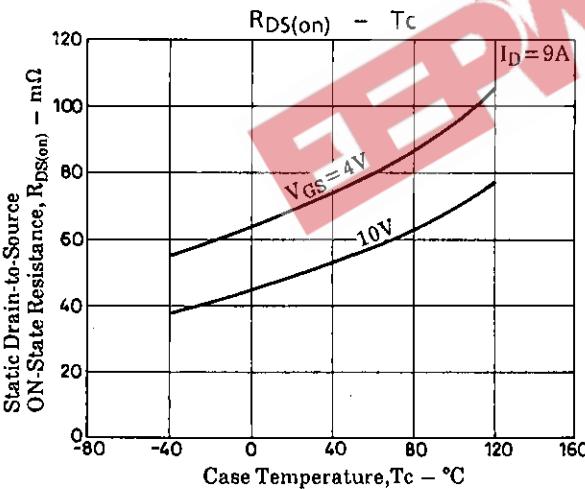
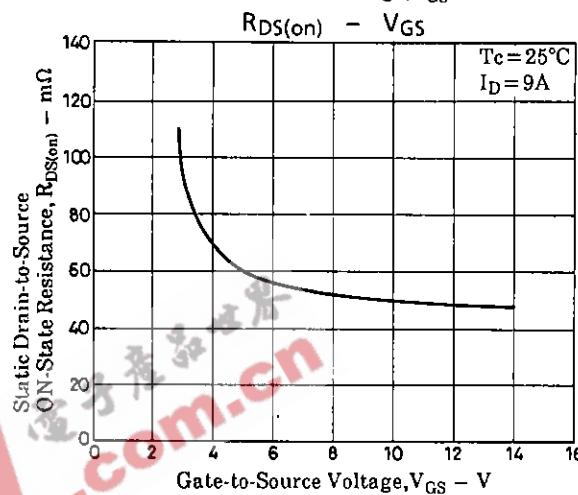
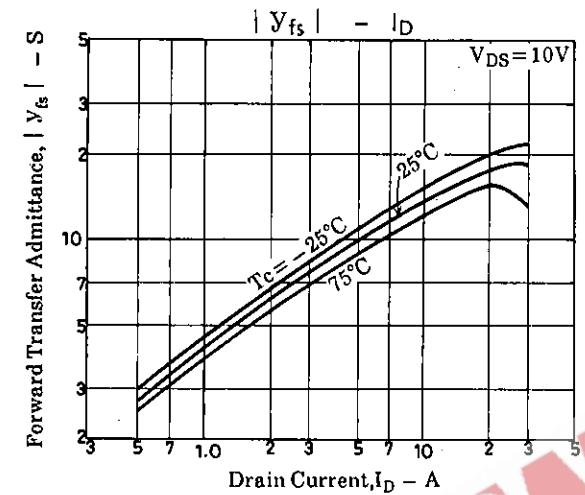
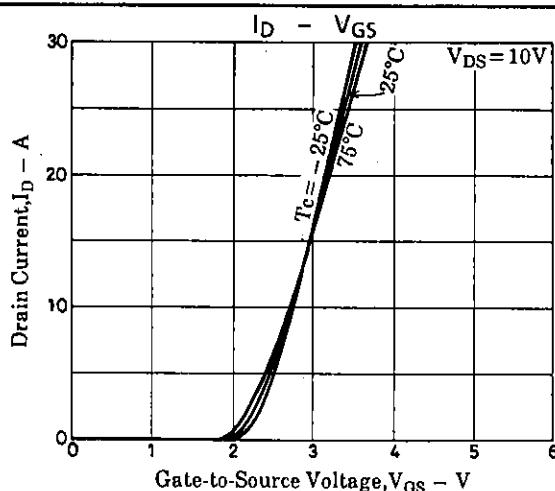
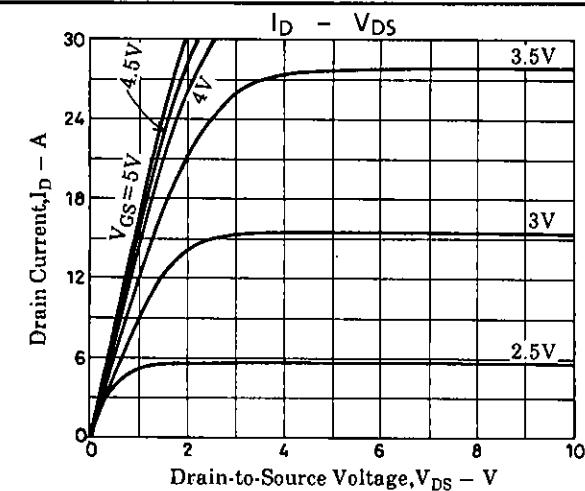
**Electrical Characteristics at Ta = 25°C**

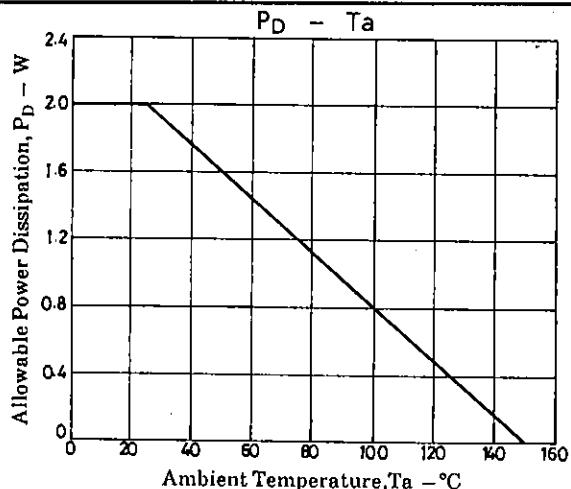
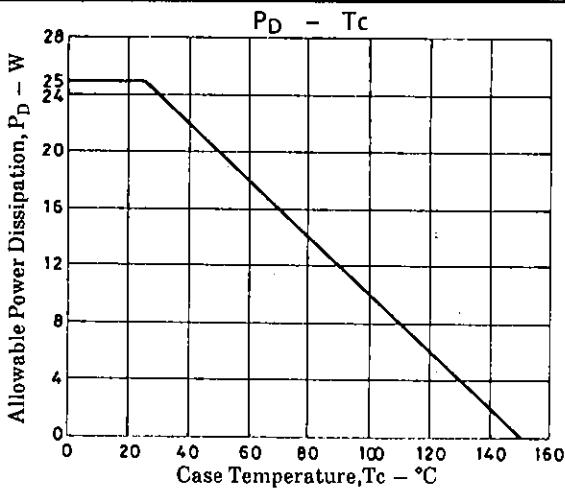
			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	60			V
G-S Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±100μA, V <sub>DS</sub> = 0	±20			V
Zero-Gate Voltage	I <sub>DSS</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0			100	μA
Drain Current						
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 9A	8	13		S
Static Drain-to-Source	R <sub>DS(on)</sub>	I <sub>D</sub> = 9A, V <sub>GS</sub> = 10V	0.05	0.07		Ω
ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 9A, V <sub>GS</sub> = 4V	0.07	0.095		Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20V, f = 1MHz	1230			pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V, f = 1MHz	330			pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 20V, f = 1MHz	65			pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.	14			ns
Rise Time	t <sub>r</sub>	"	35			ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"	250			ns
Fall Time	t <sub>f</sub>	"	120			ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 15A, V <sub>GS</sub> = 0	1.0	1.5		V

**Switching Time Test Circuit****Package Dimensions 2063A**  
(unit : mm)

SANYO : TO - 220ML

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